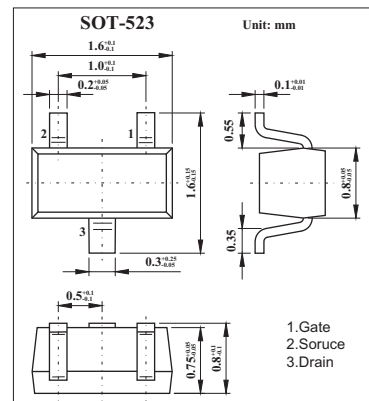
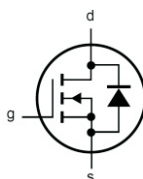


2N7002T

■ Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain-Source voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current - Continuous	I _D	115	mA
- Pulsed Note(1)		800	
Power dissipation @ TA = 25°C	P _D	0.15	W
Operating and storage junction temperature range	T _J , T _{stg}	-55 to +150	°C

Notes: 1. Pulse width limited by maximum junction temperature.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0 V, I _D =10 μA	60			V
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.76	2	
Gate-body leakage	I _{GSS}	V _{DS} =0 V, V _{GS} =±20 V			±10	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} =60 V, V _{GS} =0 V T _C = 125°C			1 500	μA
On-state drain current	I _{D(ON)}	V _{GS} =10 V, V _{DS} =7.5 V	0.5			A
Drain-source on-resistance	R _{DS(on)}	V _{GS} =10 V, I _D =500 mA @T _J = 125°C			13.5	Ω
		V _{GS} =5 V, I _D =50 mA			7.5	
Forward tran conductance	g _{fs}	V _{DS} =10 V, I _D =200 mA	80			ms
Input capacitance	C _{iss}	V _{DS} =25 V, V _{GS} =0 V, f=1 MHz		22	50	pF
Output capacitance	C _{oss}		11	25		
Reverse transfer capacitance	C _{rss}		2	7		
Turn-on Time	t _{d(on)}	V _{DD} = 30 V, R _L = 150 Ω		7.0	20	ns
Turn-off Time	t _{d(off)}	I _D =0.2 A, V _{GEN} = 10 V, R _G = 25Ω		11	20	ns

■ Marking

Marking	702
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